

FIG. 1

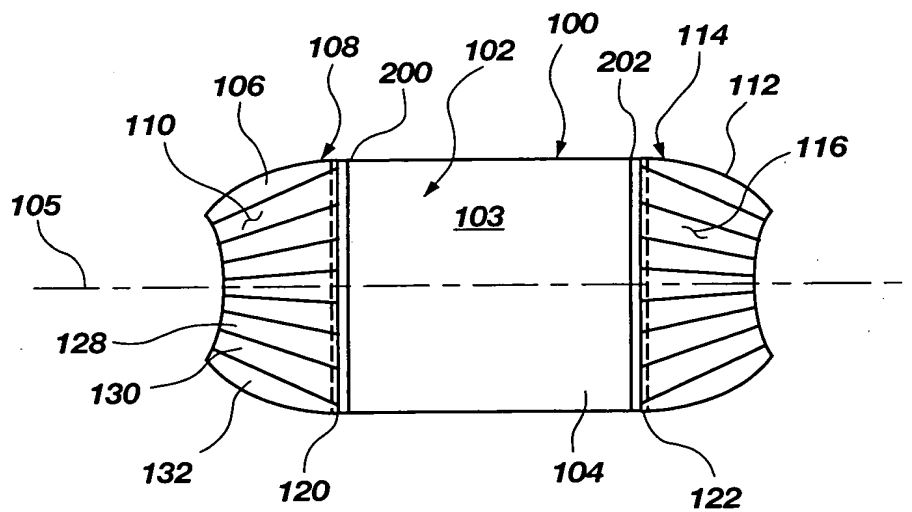


FIG. 2

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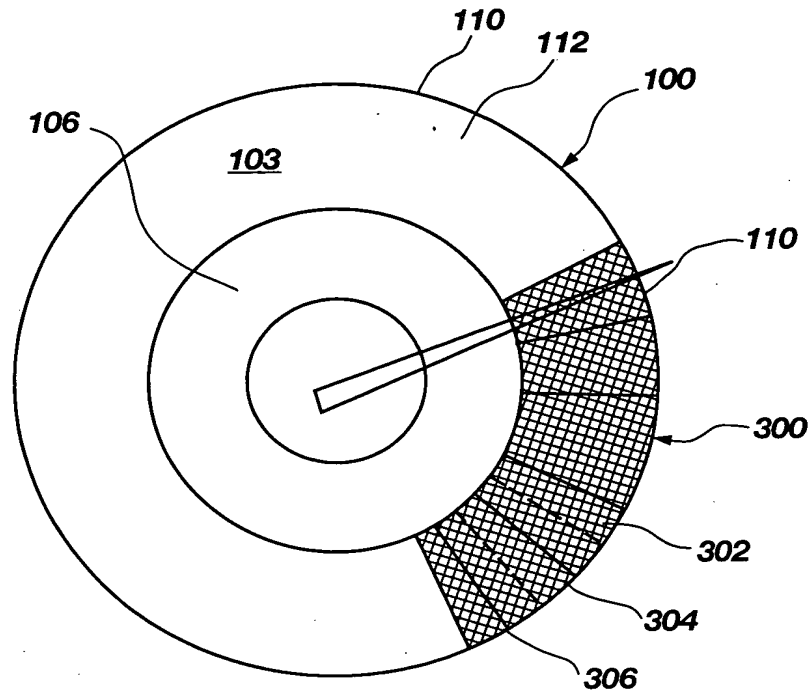


FIG. 3

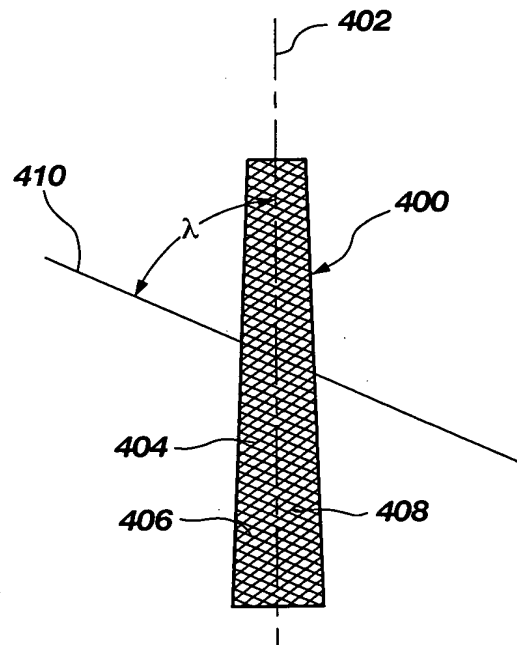


FIG. 4

A cross-sectional view of a semiconductor device. A substrate 102 is shown at the bottom. A layer 110 is formed on the substrate. A central layer 300 is formed on the layer 110. The central layer 300 is surrounded by a layer 302. A layer 600 is formed on the layer 302. A layer 602 is formed on the layer 600. A layer 604 is formed on the layer 602. A layer 606 is formed on the layer 604. A layer 610 is formed on the layer 606. A layer 612 is formed on the layer 610. A layer 608 is formed on the layer 612. A layer 304 is formed on the layer 608. A layer 306 is formed on the layer 304. A layer 102 is formed on the layer 306.

A cross-sectional view of a semiconductor device 300. The device consists of a substrate 102 with a top surface 103. A layer 110 is formed on the top surface 103. On top of layer 110, there is a layer 702. A layer 704 is formed on top of layer 702. A layer 306 is formed on top of layer 704. A layer 302 is formed on top of layer 306. A layer 304 is formed on top of layer 302. A layer 706 is formed on top of layer 304. A layer 300 is formed on top of layer 706.

FIG. 7



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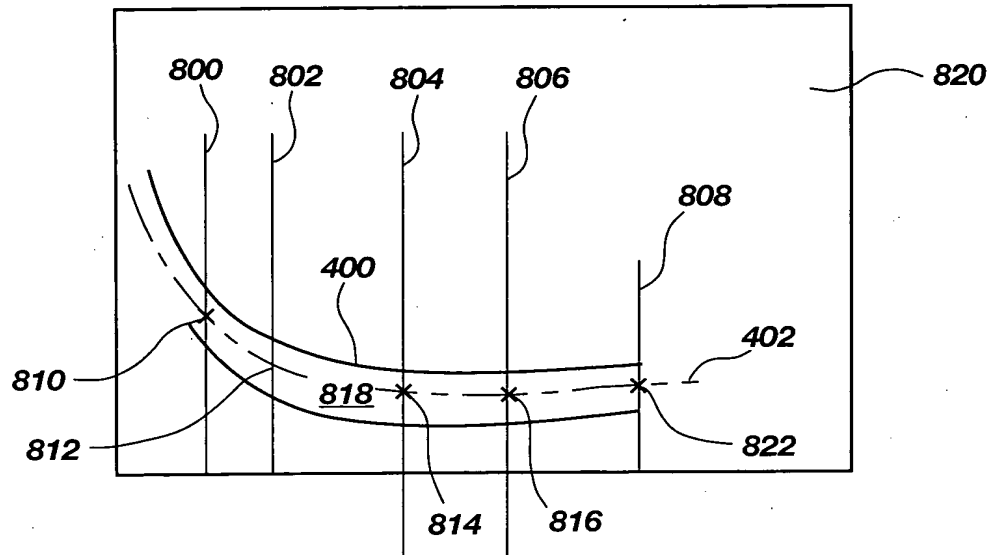


FIG. 8

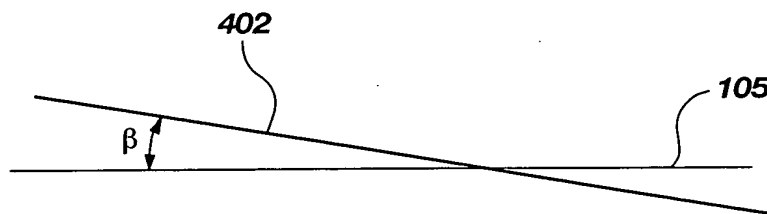


FIG. 9

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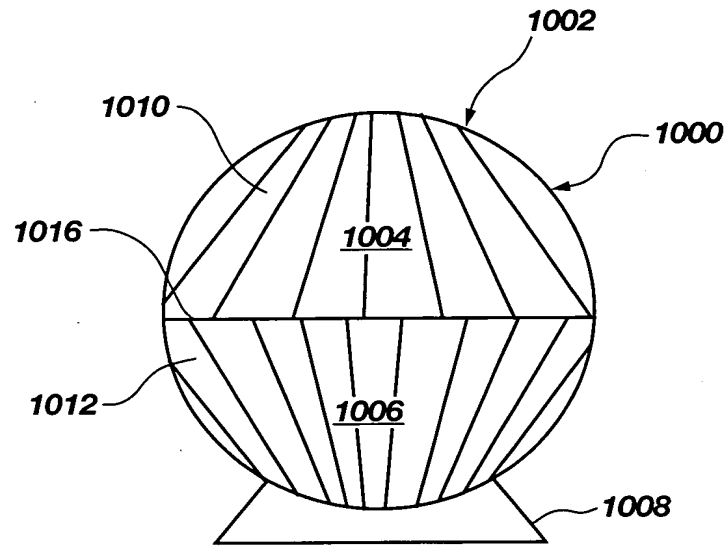


FIG. 10